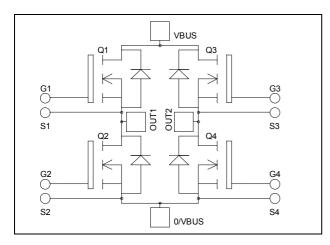


Full - Bridge MOSFET Power Module

$$\begin{split} V_{DSS} &= 1200 V \\ R_{DSon} &= 290 m \Omega \text{ typ } \text{ } \text{ } \text{ } \text{Tj} = 25^{\circ} \text{C} \\ I_D &= 34 \text{A} \text{ } \text{ } \text{ } \text{ } \text{Tc} = 25^{\circ} \text{C} \end{split}$$



0/VBU

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Power MOS 7[®] FREDFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Fast intrinsic reverse diode
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
$V_{ m DSS}$	Drain - Source Breakdown Voltage		1200	V
Ţ	Continuous Drain Current	$T_c = 25$ °C	34	
I_D	Continuous Drain Current	$T_c = 80^{\circ}C$	25	A
I_{DM}	Pulsed Drain current		136	
V_{GS}	Gate - Source Voltage		±30	V
R _{DSon}	Drain - Source ON Resistance		348	mΩ
P_{D}	Maximum Power Dissipation $T_c = 25^{\circ}C$		780	W
I_{AR}	Avalanche current (repetitive and non repetitive)		22	A
E_{AR}	Repetitive Avalanche Energy		50	m I
E_{AS}	Single Pulse Avalanche Energy		3000	mJ

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 1200V$	$T_j = 25^{\circ}C$			350	μА
		$V_{GS} = 0V, V_{DS} = 1000V$	$T_j = 125$ °C			1500	
R _{DS(on)}	Drain – Source on Resistance	$V_{GS} = 10V, I_D = 17A$			290	348	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 5mA$		3		5	V
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$				±150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Тур	Max	Unit
Ciss	Input Capacitance	$V_{GS} = 0V$		10.3		
C_{oss}	Output Capacitance	$V_{DS} = 25V$		1.54		nF
C_{rss}	Reverse Transfer Capacitance	f=1MHz		0.26		
Q_{g}	Total gate Charge	$V_{GS} = 10V$		374		nC
Q_{gs}	Gate – Source Charge	$V_{Bus} = 600V$		48		
Q_{gd}	Gate – Drain Charge	$I_D = 34A$		240		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C		20		
$T_{\rm r}$	Rise Time	$\begin{split} V_{GS} &= 15 V \\ V_{Bus} &= 800 V \\ I_D &= 34 A \\ R_G &= 2.5 \Omega \end{split}$		15		ns
$T_{d(off)}$	Turn-off Delay Time			160		
T_{f}	Fall Time			45		
Eon	Turn-on Switching Energy	Inductive switching @ 25°C		1980		1
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		1371		μJ
Eon	Turn-on Switching Energy	Inductive switching @ 125°C		3131		т
E_{off}	Turn-off Switching Energy	$V_{GS} = 15V, V_{Bus} = 800V$ $I_D = 34A, R_G = 2.5\Omega$		1714		μJ

Source - Drain diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_S	Continuous Source current		$Tc = 25^{\circ}C$			34	A
	(Body diode)		$Tc = 80^{\circ}C$			25	А
V_{SD}	Diode Forward Voltage	$V_{GS} = 0V, I_S = -34A$				1.3	V
dv/dt	Peak Diode Recovery					18	V/ns
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$			320	ns
	reverse receivery Time	$I_S = -34A$ $V_R = 600V$	$T_j = 125$ °C			650	115
Q _{rr}	Reverse Recovery Charge	$di_{S}/dt = 200A/\mu s$	$T_j = 25$ °C		4		μC
	reverse receivery charge		$T_j = 125$ °C		14		μС

• dv/dt numbers reflect the limitations of the circuit rather than the device itself.

 $I_{S} \leq \text{--} \ 34A \qquad di/dt \leq 700 A/\mu s \qquad V_{R} \leq V_{DSS} \qquad T_{j} \leq 150 ^{\circ} C$

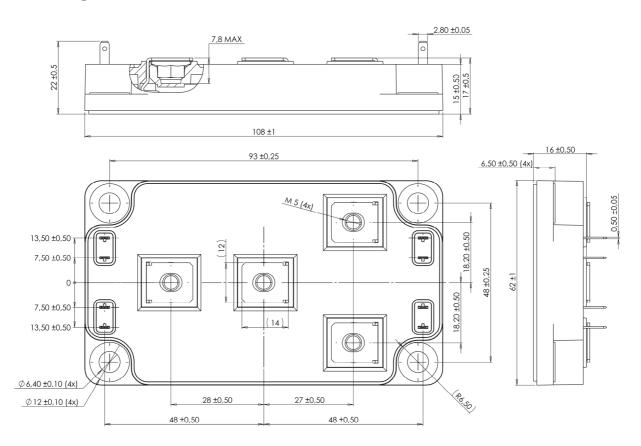
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Thermal and package characteristics

Symbol	Characteristic		Min	Тур	Max	Unit				
R_{thJC}	Junction to Case Thermal Resistance					0.16	°C/W			
V_{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz			4000			V			
T_{J}	Operating junction temperature range	Departing junction temperature range				150				
T_{STG}	Storage Temperature Range			-40		125	25 °C			
$T_{\rm C}$	Operating Case Temperature					100				
Torque	Mounting torque	To heatsink	M6	3		5	N.m			
		For terminals	M5	2		3.5	11.111			
Wt	Package Weight					300	g			

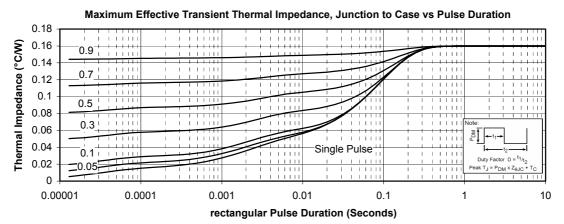
SP6 Package outline (dimensions in mm)

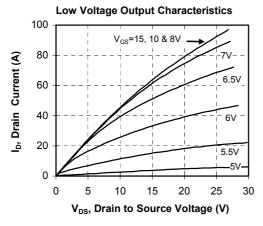


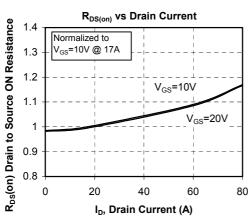
See application note APT0601 - Mounting Instructions for SP6 Power Modules on www.microsemi.com

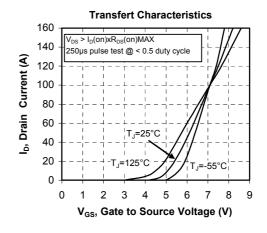


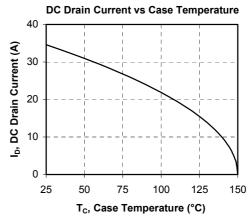
Typical Performance Curve



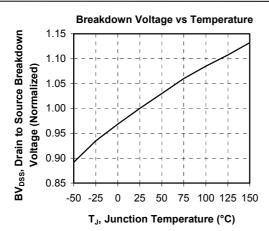


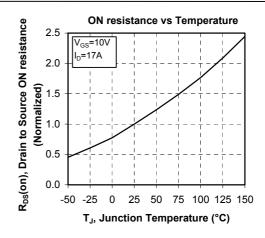


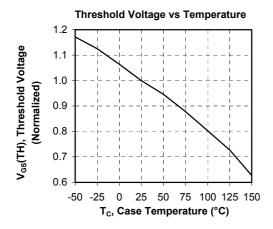


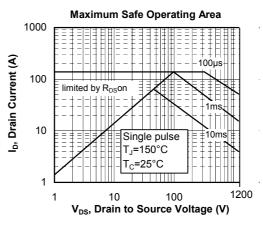


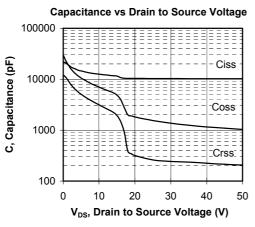


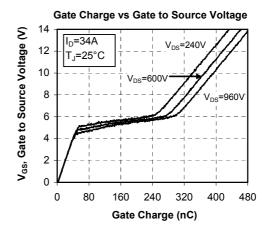




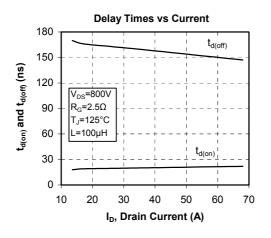


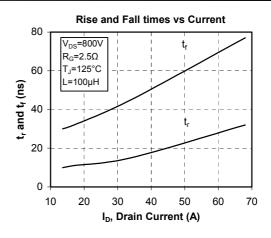


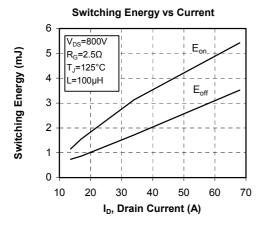


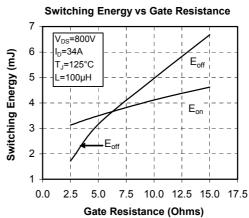


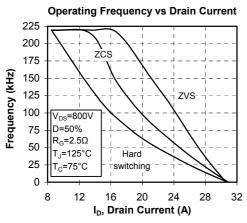


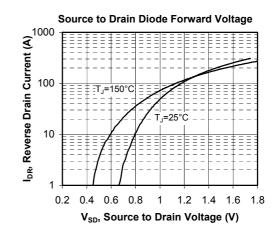












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